

ABSTRACT OF THE DISCLOSURE

A nitride semiconductor laser device chip has a nitride semiconductor stacked-layered structure including an n-type layer, an active layer and a p-type layer stacked successively on a main surface of a nitride semiconductor substrate. A ridge stripe structure is formed in a portion of the p-type layer. The chip has a length L1 of more than 500 μm in a longitudinal direction of the stripe structure and a length L2 of more than 200 μm in a width direction of the stripe structure, and L1/L2 is more than 2.5.